## Application No. 09/497,508

East Search 5/9/01

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Search	LINO	Hits	illext/Search		Data Bases
			("438/512,515,517,526,539,554,555,563		USPAT; EPO; JPO;
IS&R	Ll	1932	").CCLS.	5/9/01 8:41	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L2	314	1 and polycrystalline	5/9/01 8:42	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L3	44	2 and amorphous adj silicon	5/9/01 8:43	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L6	6	3 and (ni nickel)	5/9/01 8:46	Derwent; IBM TDB
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NUSPANI.	<b>建設</b> Date	鐵Kage選	Title	Sel/Sup	CI/Sub	Inventor :
			Implantation method having improved			
US 5354697 A	19941011		material purity	438/514	438/526 ; 438/531	Oostra, Doeke J., et al.
			Methods for forming epitaxial self-			
			aligned calcium silicide contacts and			
US 5248633 A	19930928		structures	438/526	438/533	Morar, John F., et al.
05 02 10055 11	19930920	•	Sit detailes	130/320	150/555	OKABAYASHI,
	·		METHOD FOR FORMING			HIDEKAZU, SAITO,
JP 02137326 A	19900525				438/512	
JP 0213/326 A	19900323		MICROSCOPIC STRUCTURE		438/312	SHUICHI, et al.
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					<u> </u>	USPAT; EPO; JPO;
BRS	L1	31644	thin adj film adj transistor or tft		5/9/01 9:53	
				1		USPAT; EPO; JPO;
BRS	L2	227	1 and solar adj cell	l	5/9/01 9:54	
						USPAT; EPO; JPO;
BRS	L4	51	2 and (ni nickel)	_	5/9/01 9:55	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L5	10	4 and amorphous adj silicon adj film		5/9/01 9:56	
						USPAT; EPO; JPO;
BRS	L6	5 .	5 and polycrystalline		5/9/01 9:57	Derwent; IBM TDB

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USPAT	Date.	Page	Title	Cl/Sub	Cl/Sub	Inventor.
			Polycrystalline silicon semiconductor			
			having an amorphous silicon buffer		257/431; 257/461;	i
US 5667597 A	19970916	15	layer	136/258	257/49	Ishihara, Shunichi
			Method for forming single silicon		117/45 ; 117/902 ;	
US 5893948 A	19990413	13	crystals using nucleation sites	117/43	117/933	Nickel, Norbert H., et al.
			Method and apparatus for continuously			
			forming functional deposited films		118/718;	
			with a large area by a microwave plasma		118/723ME ;	
US 5527391 A	19960618	- 68	CVD method	118/719	118/723MW	Echizen, Hiroshi, et al.
			Apparatus for continuously forming a		118/723ME ;	
			large area functional deposit film	<u> </u>	118/725 ; 118/730 ;	
1			including microwave transmissive		118/733 ; 136/249 ;	·
US 5296036 A	19940322	59	member transfer mean	118/718	136/258 ; 156/345	Matsuyama, Jinsho, et al.
			Method for continuously forming			
			functional deposited films with a large		136/258 ; 427/248.1	
			area by a microwave plasma CVD		; 427/314 ;	·
US 5114770 A	19920519	69	method	427/575	427/398.1	Echizen, Hiroshi, et al.

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Search	L No.	Hits Text Search		Data Bases
		(("5677549") or ("5656825") or		
	1 1	("5646424") or ("5744824") or		
	1 . 1	("5705829") or ("5700333") or		USPAT; EPO; JPO;
IS&R	7	("5696388")).PN.	5/9/01 10:28	Derwent; IBM TDB
-		(("5624851") or ("5620910") or		USPAT; EPO; JPO;
IS&R	4	("5616506") or ("5614733")).PN.	5/9/01 10:40	Derwent; IBM TDB
		(("5508533") or ("5501989") or		
	1 1	("5654203") or ("5663077") or		
	1	("5643826") or ("5543352") or		
	1 1	("5426064") or ("5481121") or		ŀ
		("5488000") or ("5492843") or	Ì	USPAT; EPO; JPO;
IS&R	11	("5534716")).PN.	5/9/01 10:50	Derwent; IBM TDB
•		(("5595923") or ("5589694") or		
		("5569610") or ("5580792") or		
		("5606179") or ("5605846") or		
	f l	("5604360") or ("5595944") or		USPAT; EPO; JPO;
IS&R	9	("5612250")).PN.	5/9/01 11:04	Derwent; IBM TDB
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USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
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